

N-channel enhancement mode TrenchMOS™ transistor

IRFZ24N

GENERAL DESCRIPTION

N-channel enhancement mode standard level field-effect power transistor in a plastic envelope using 'trench' technology. The device features very low on-state resistance and has integral zener diodes giving ESD protection up to 2kV. It is intended for use in switched mode power supplies and general purpose switching applications.

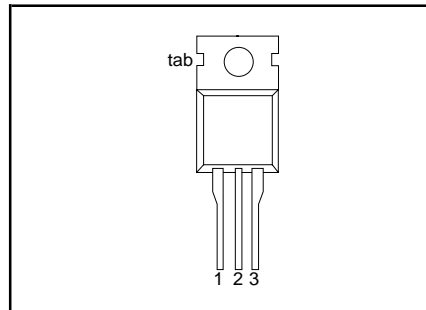
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|--------------|---|------|------|
| V_{DS} | Drain-source voltage | 55 | V |
| I_D | Drain current (DC) | 17 | A |
| P_{tot} | Total power dissipation | 45 | W |
| T_j | Junction temperature | 175 | °C |
| $R_{DS(ON)}$ | Drain-source on-state resistance $V_{GS} = 10\text{ V}$ | 70 | mΩ |

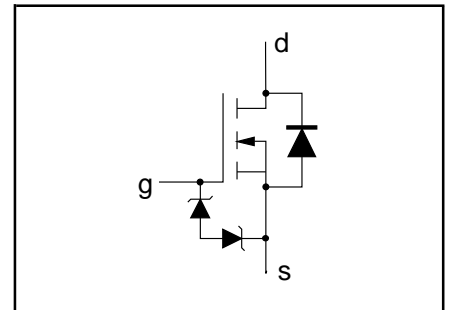
PINNING - TO220AB

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | gate |
| 2 | drain |
| 3 | source |
| tab | drain |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|----------------|----------------------------------|--------------------------------------|------|------|------|
| V_{DS} | Drain-source voltage | - | - | 55 | V |
| V_{DGR} | Drain-gate voltage | $R_{GS} = 20\text{ k}\Omega$ | - | 55 | V |
| $\pm V_{GS}$ | Gate-source voltage | - | - | 20 | V |
| I_D | Drain current (DC) | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 17 | A |
| I_D | Drain current (DC) | $T_{mb} = 100\text{ }^\circ\text{C}$ | - | 12 | A |
| I_{DM} | Drain current (pulse peak value) | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 68 | A |
| P_{tot} | Total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 45 | W |
| T_{stg}, T_j | Storage & operating temperature | - | - 55 | 175 | °C |

ESD LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------|---|-----------------------------------|------|------|------|
| V_C | Electrostatic discharge capacitor voltage, all pins | Human body model (100 pF, 1.5 kΩ) | - | 2 | kV |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|--|-------------|------|------|------|
| $R_{th\ j-mb}$ | Thermal resistance junction to mounting base | - | - | 3.3 | K/W |
| $R_{th\ j-a}$ | Thermal resistance junction to ambient | in free air | 60 | - | K/W |

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STATIC CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------------|----------------------------------|---|-----------------|---------------|-----------------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0\text{ V}$; $I_D = 0.25\text{ mA}$; $T_j = -55^\circ\text{C}$ | 55 50 | - - | - - | V V |
| $V_{GS(TO)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$; $I_D = 1\text{ mA}$; $T_j = 175^\circ\text{C}$ $T_j = -55^\circ\text{C}$ | 2.0 1.0 - | 3.0 - - | 4.0 - 4.4 | V V V |
| I_{DSS} | Zero gate voltage drain current | $V_{DS} = 55\text{ V}$; $V_{GS} = 0\text{ V}$; $T_j = 175^\circ\text{C}$ | - | 0.05 | 10 | μA |
| I_{GSS} | Gate source leakage current | $V_{GS} = \pm 10\text{ V}$; $V_{DS} = 0\text{ V}$; $T_j = 175^\circ\text{C}$ | - | 0.04 | 500 | μA |
| $\pm V_{(BR)GSS}$ | Gate source breakdown voltage | $I_G = \pm 1\text{ mA}$; $T_j = 175^\circ\text{C}$ | - | - | 1 | μA |
| $R_{DS(ON)}$ | Drain-source on-state resistance | $V_{GS} = 10\text{ V}$; $I_D = 10\text{ A}$; $T_j = 175^\circ\text{C}$ | 16 | - | 20 | μA |
| | | | - | 60 | 70 | m Ω |
| | | | - | - | 157 | m Ω |

DYNAMIC CHARACTERISTICS

 $T_{mb} = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|------------|----------------------------|---|------|------|------|------|
| g_{fs} | Forward transconductance | $V_{DS} = 25\text{ V}$; $I_D = 10\text{ A}$ | 1 | - | - | S |
| C_{iss} | Input capacitance | $V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$; $f = 1\text{ MHz}$ | - | 365 | 500 | pF |
| C_{oss} | Output capacitance | | - | 110 | 135 | pF |
| C_{rss} | Feedback capacitance | | - | 60 | 85 | pF |
| Q_g | Total gate charge | $V_{DD} = 44\text{ V}$; $I_D = 20\text{ A}$; $V_{GS} = 10\text{ V}$ | - | - | 19 | nC |
| Q_{gs} | Gate-source charge | | - | - | 5.2 | nC |
| Q_{gd} | Gate-drain (miller) charge | | - | - | 7.2 | nC |
| t_{don} | Turn-on delay time | $V_{DD} = 30\text{ V}$; $I_D = 10\text{ A}$; $V_{GS} = 10\text{ V}$; $R_G = 10\text{ }\Omega$ | - | 9 | 14 | ns |
| t_r | Turn-on rise time | | - | 16 | 21 | ns |
| t_{doff} | Turn-off delay time | Resistive load | - | 14 | 25 | ns |
| t_f | Turn-off fall time | | - | 13 | 20 | ns |
| L_d | Internal drain inductance | Measured from contact screw on tab to centre of die | - | 3.5 | - | nH |
| L_d | Internal drain inductance | Measured from drain lead 6 mm from package to centre of die | - | 4.5 | - | nH |
| L_s | Internal source inductance | Measured from source lead 6 mm from package to source bond pad | - | 7.5 | - | nH |

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

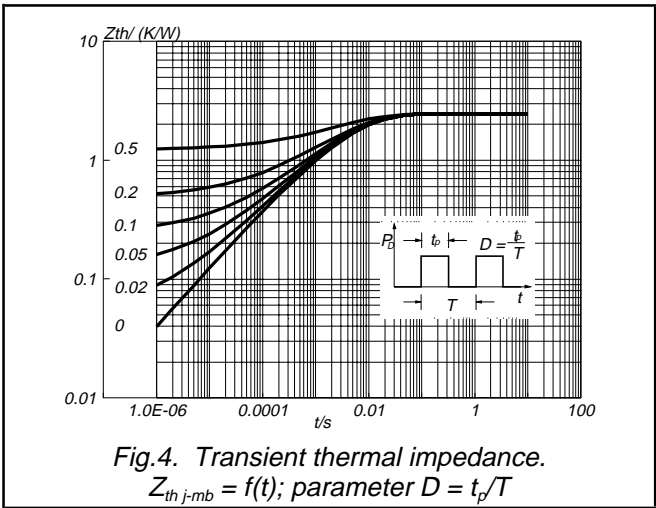
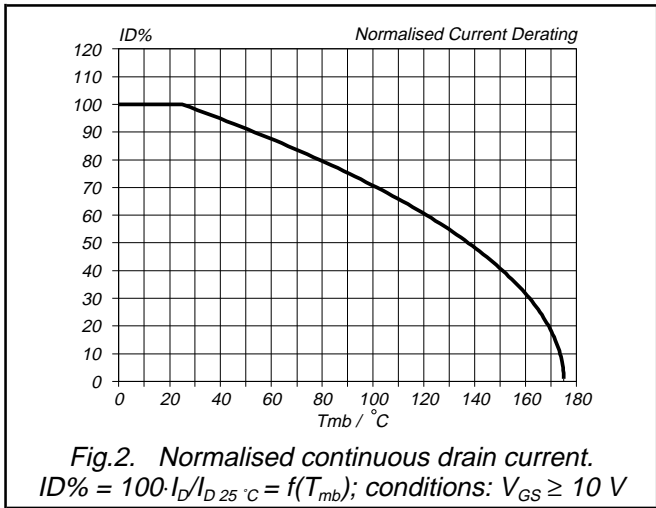
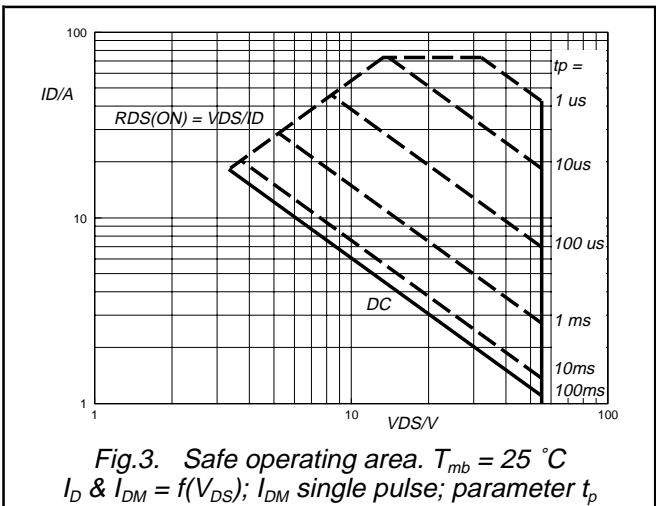
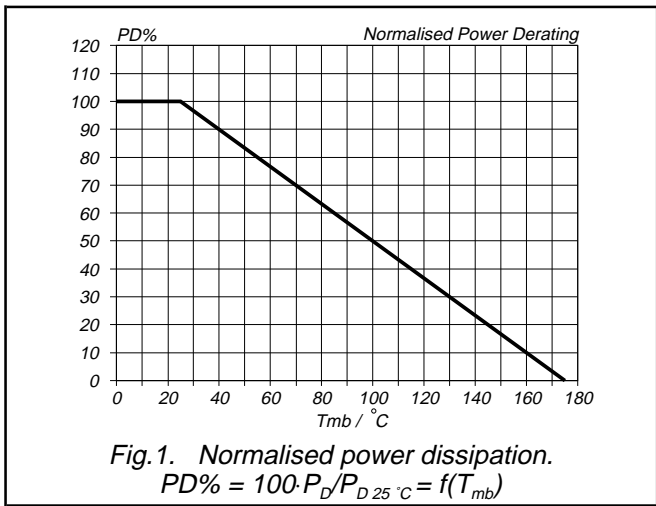
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|----------------------------------|--|------|------|------|---------------|
| I_{DR} | Continuous reverse drain current | | - | - | 17 | A |
| I_{DRM} | Pulsed reverse drain current | | - | - | 68 | A |
| V_{SD} | Diode forward voltage | $I_F = 19.7\text{ A}$; $V_{GS} = 0\text{ V}$ | - | 0.95 | 1.2 | V |
| t_{rr} | Reverse recovery time | $I_F = 19.7\text{ A}$; $-dI_F/dt = 100\text{ A}/\mu\text{s}$; $V_{GS} = -10\text{ V}$; $V_R = 30\text{ V}$ | - | 32 | - | ns |
| Q_{rr} | Reverse recovery charge | | - | 0.12 | - | μC |

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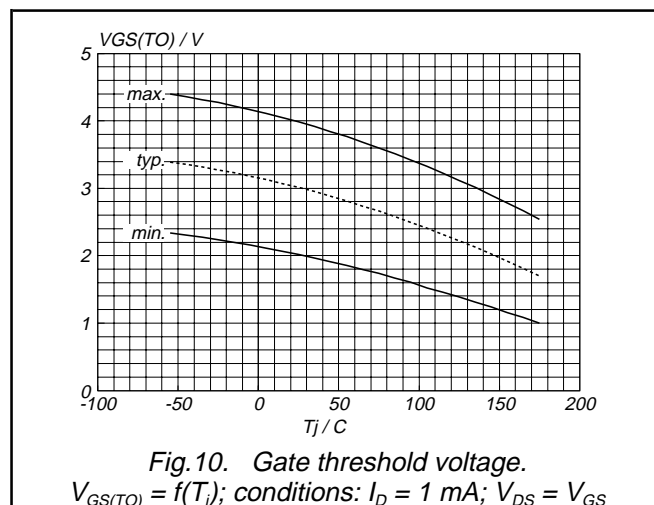
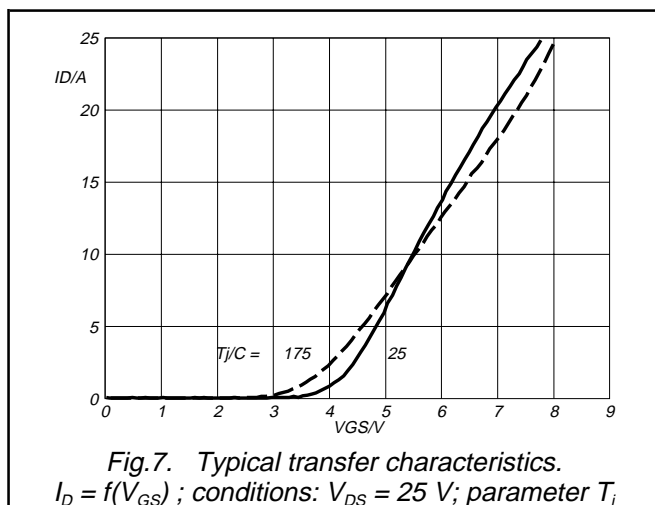
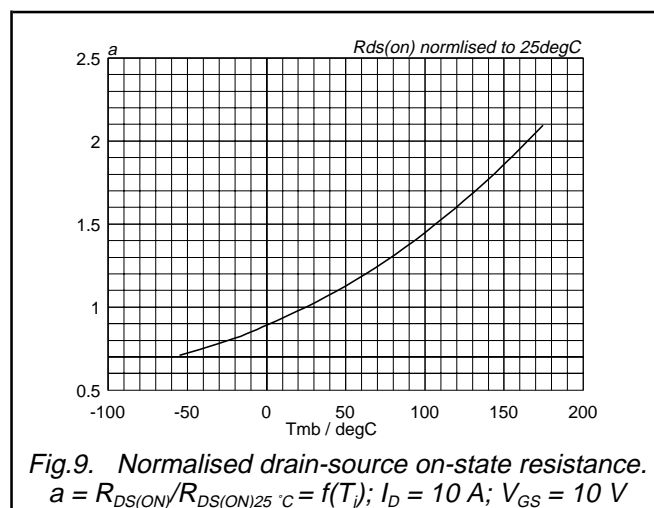
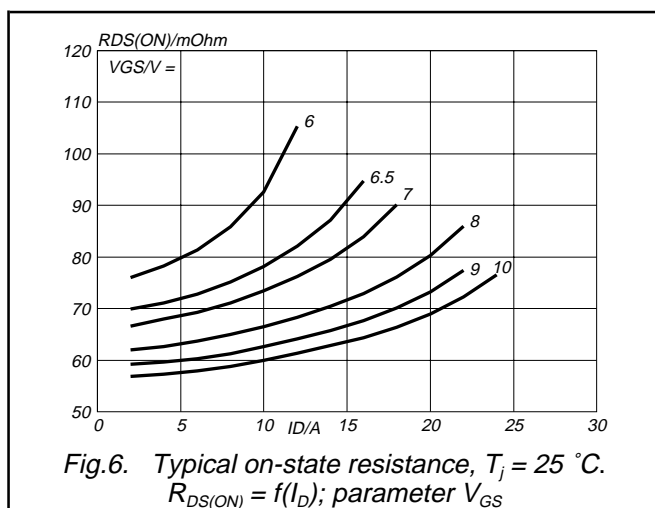
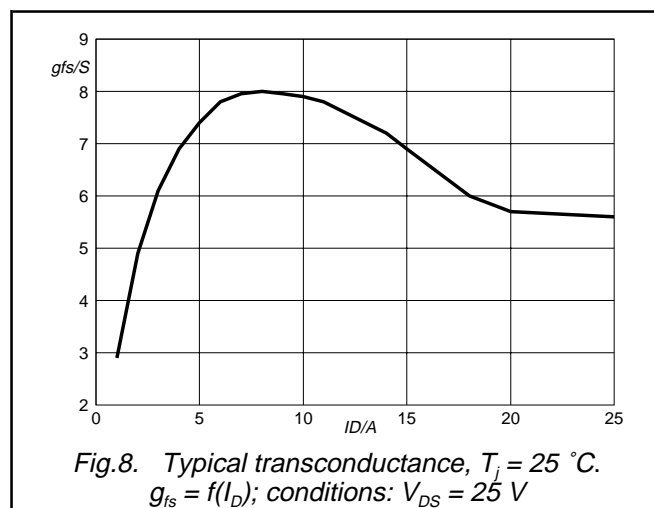
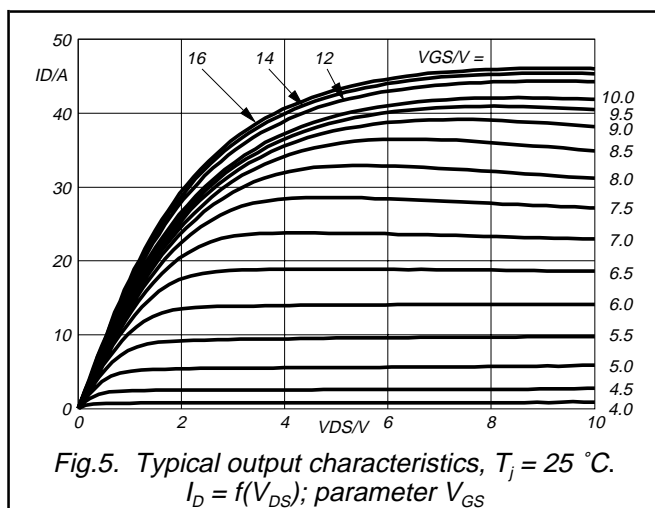
AVALANCHE LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|---|---|------|------|------|------|
| W_{DSS} | Drain-source non-repetitive unclamped inductive turn-off energy | $I_D = 10\text{ A}$; $V_{DD} \leq 25\text{ V}$; $V_{GS} = 10\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $T_{mb} = 25\text{ }^\circ\text{C}$ | - | - | 30 | mJ |



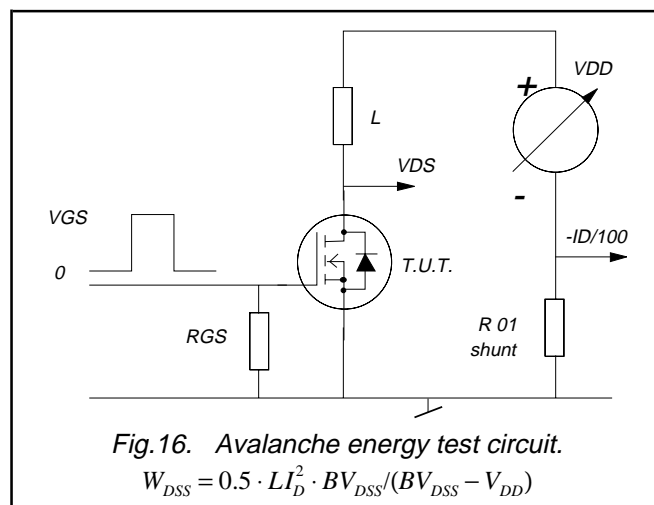
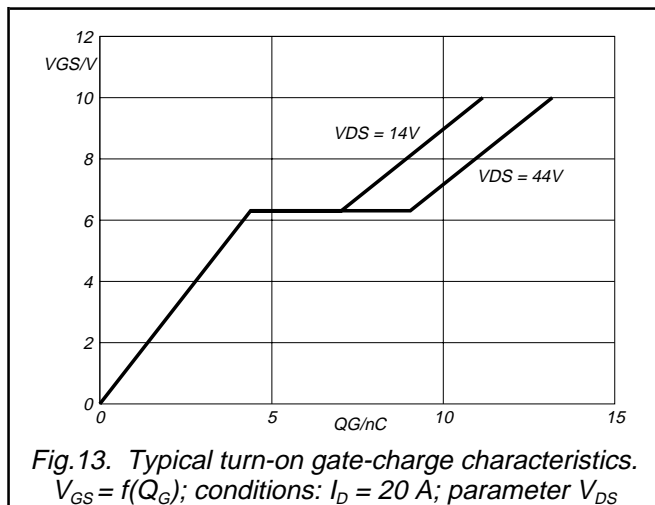
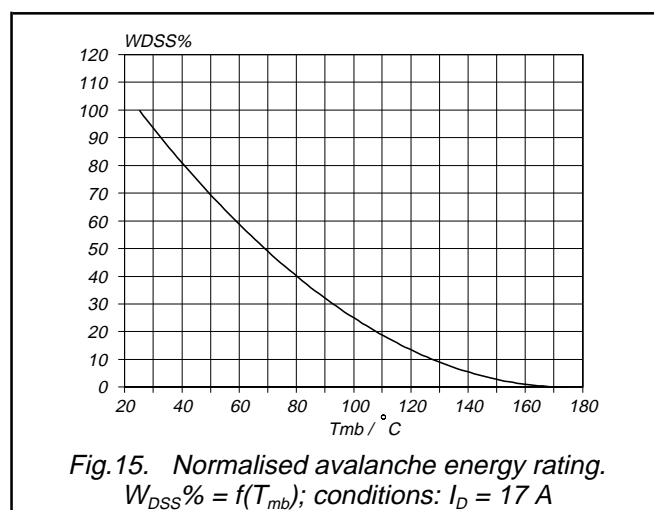
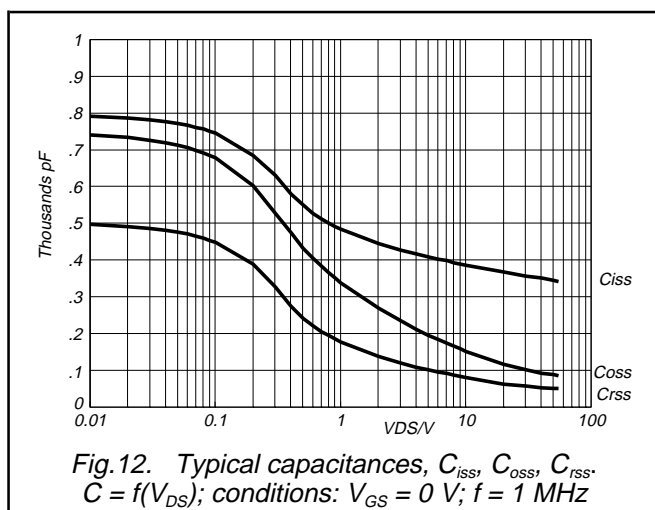
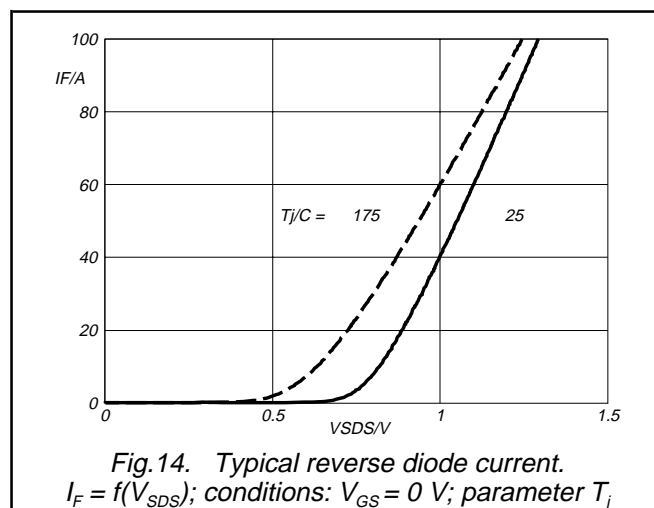
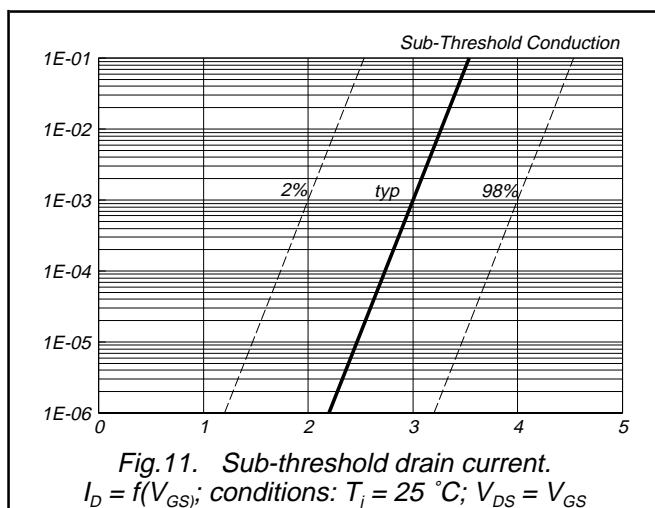
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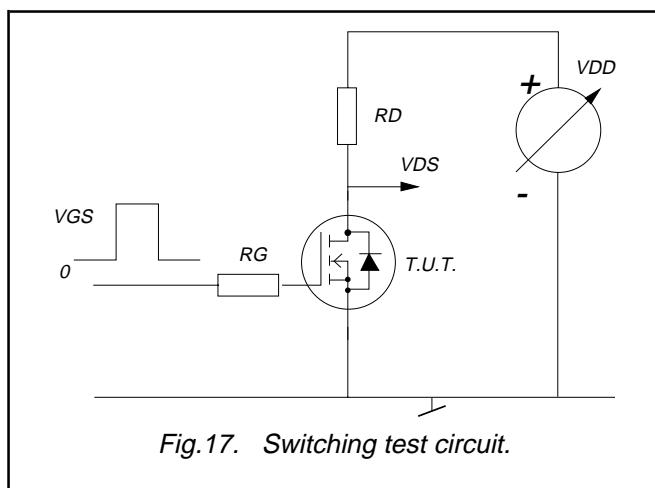


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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

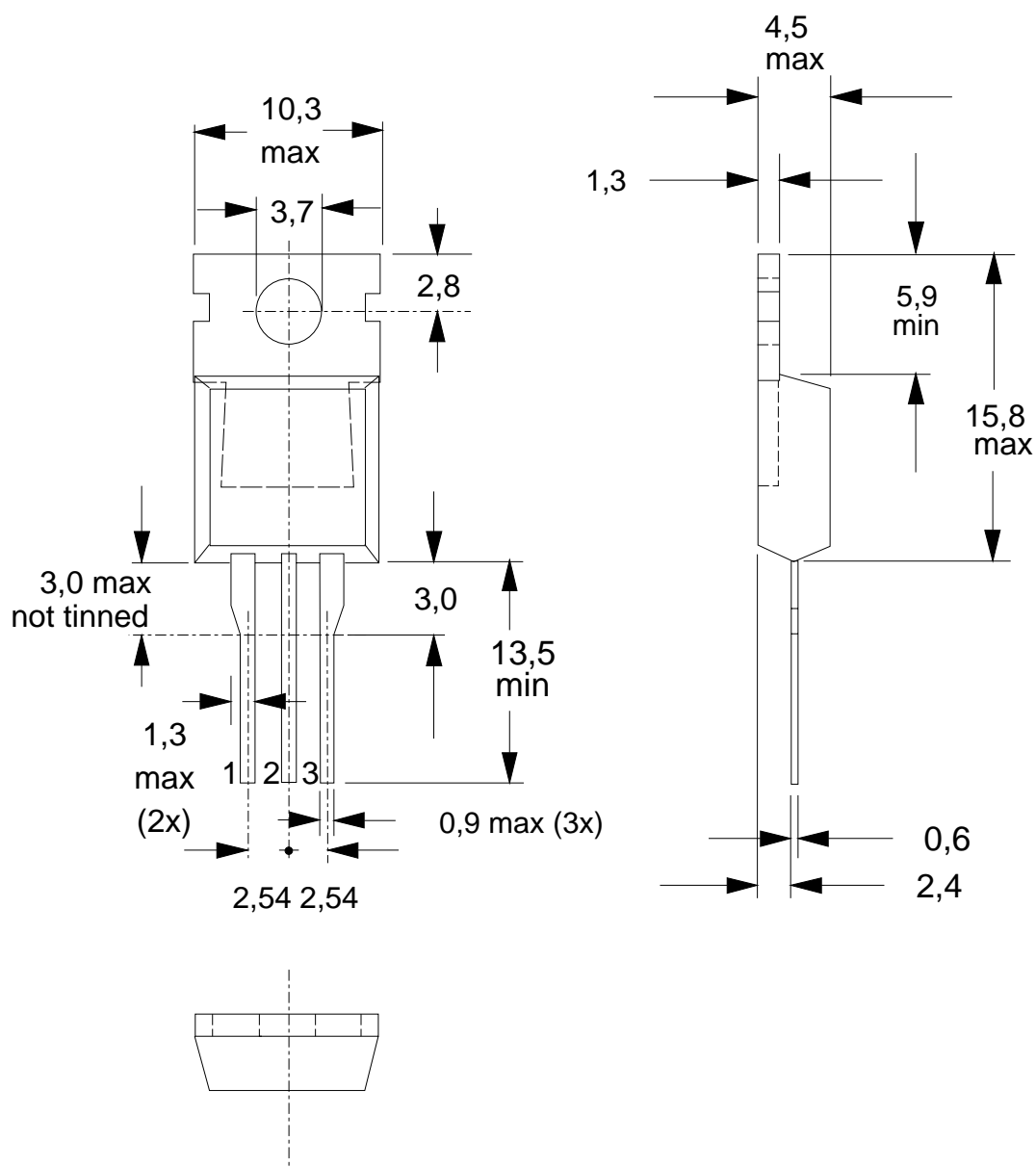


Fig.18. SOT78 (TO220AB); pin 2 connected to mounting base.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to mounting instructions for SOT78 (TO220) envelopes.
3. Epoxy meets UL94 V0 at 1/8".

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IRFZ24N**DEFINITIONS**

| Data sheet status | |
|--|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |
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